Martin P Seah

List of Publications by Year
in descending order

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230 papers	10,108 citations	28274 55 h-index	43889 91 g-index
231 all docs	231 docs citations	231 times ranked	6231 citing authors

#	Article	IF	Citations
1	OrbiSIMS metrology Part I: Optimisation of the target potential and collision cell pressure. Surface and Interface Analysis, 2022, 54, 331-340.	1.8	6
2	Argon cluster cleaning of Ga⁺ FIBâ€milled sections of organic and hybrid materials. Surface and Interface Analysis, 2020, 52, 327-334.	1.8	7
3	Argon Cluster Sputtering Reveals Internal Chemical Distribution in Submicron Polymeric Particles. Journal of Physical Chemistry C, 2020, 124, 23752-23763.	3.1	6
4	Summary of ISO/TC 201 Standard: ISO 22415â€"Surface chemical analysisâ€"Secondary ion mass spectrometryâ€"Method for determining yield volume in argon cluster sputter depth profiling of organic materials. Surface and Interface Analysis, 2019, 51, 1018-1020.	1.8	2
5	SIMS of organic layers with unknown matrix parameters: Locating the interface in dual beam argon gas cluster depth profiles. Surface and Interface Analysis, 2019, 51, 1332-1341.	1.8	4
6	Chemical Imaging of Buried Interfaces in Organicâ€“Inorganic Devices Using Focused Ion Beam-Time-of-Flight-Secondary-Ion Mass Spectrometry. ACS Applied Materials & Interfaces, 2019, 11, 4500-4506.	8.0	6
7	The matrix effect in secondary ion mass spectrometry. Applied Surface Science, 2018, 439, 605-611.	6.1	23
8	Analytic function to describe interfaces and resolution consistency in sputter depth profiling. Surface and Interface Analysis, 2018, 50, 123-127.	1.8	2
9	Semiempirical Rules To Determine Drug Sensitivity and Ionization Efficiency in Secondary Ion Mass Spectrometry Using a Model Tissue Sample. Analytical Chemistry, 2016, 88, 11028-11036.	6.5	15
10	Systematic Temperature Effects in the Argon Cluster Ion Sputter Depth Profiling of Organic Materials Using Secondary Ion Mass Spectrometry. Journal of the American Society for Mass Spectrometry, 2016, 27, 1411-1418.	2.8	7
11	Determination of the sputtering yield of cholesterol using Arn+ and C60+(+) cluster ions. Analyst, The, 2016, 141, 4893-4901.	3.5	1
12	Peptide Fragmentation and Surface Structural Analysis by Means of ToF-SIMS Using Large Cluster Ion Sources. Analytical Chemistry, 2016, 88, 3592-3597.	6.5	59
13	Sampling Depths, Depth Shifts, and Depth Resolutions for Bi_n⁺ Ion Analysis in Argon Gas Cluster Depth Profiles. Journal of Physical Chemistry B, 2016, 120, 2604-2611.	2.6	14
14	Depth resolution at organic interfaces sputtered by argon gas cluster ions: the effect of energy, angle and cluster size. Analyst, The, 2015, 140, 6508-6516.	3.5	21
15	Angle Dependence of Argon Gas Cluster Sputtering Yields for Organic Materials. Journal of Physical Chemistry B, 2015, 119, 3297-3303.	2.6	26
16	Sputtering Yields for Mixtures of Organic Materials Using Argon Gas Cluster Ions. Journal of Physical Chemistry B, 2015, 119, 13433-13439.	2.6	19
17	Argon cluster size-dependence of sputtering yields of polymers: molecular weights and the universal equation. Surface and Interface Analysis, 2015, 47, 169-172.	1.8	10
18	Quantitative characterization of defect size in graphene using Raman spectroscopy. Applied Physics Letters, 2014, 105, .	3.3	61

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19	Correction to VAMAS Interlaboratory Study for Desorption Electrospray Ionization Mass Spectrometry (DESI MS) Intensity Repeatability and Constancy. Analytical Chemistry, 2014, 86, 11472-11472.	6.5	0
20	Summary of ISO/TC 201 standard: ISO 18115â€2:2013 â€“ surface chemical analysis â€“ vocabulary â€“ terms used in scanning probe microscopy. Surface and Interface Analysis, 2014, 46, 361-364.	1.8	6
21	Summary of ISO/TC 201 Standard: ISO 18115â€1:2013 â€“ Surface chemical analysis â€“ Vocabulary â€“ General terms and terms used in spectroscopy. Surface and Interface Analysis, 2014, 46, 357-360.	1.8	8
22	VAMAS Interlaboratory Study for Desorption Electrospray Ionization Mass Spectrometry (DESI MS) Intensity Repeatability and Constancy. Analytical Chemistry, 2014, 86, 9603-9611.	6.5	38
23	Measurement of the roughness of nano-scale surfaces, both unannealed and with limited anneal, by atomic force microscopy. Measurement Science and Technology, 2014, 25, 105001.	2.6	2
24	Universal Equation for Argon Cluster Size-Dependence of Secondary Ion Spectra in SIMS of Organic Materials. Journal of Physical Chemistry C, 2014, 118, 12862-12872.	3.1	33
25	Electron Flood Gun Damage Effects in 3D Secondary Ion Mass Spectrometry Imaging of Organics. Journal of the American Society for Mass Spectrometry, 2014, 25, 1565-1571.	2.8	15
26	Depth Profiling and Melting of Nanoparticles in Secondary Ion Mass Spectrometry (SIMS). Journal of Physical Chemistry C, 2013, 117, 16042-16052.	3.1	26
27	Depth Resolution, Angle Dependence, and the Sputtering Yield of Irganox 1010 by Coronene Primary Ions. Journal of Physical Chemistry B, 2013, 117, 11885-11892.	2.6	8
28	Universal Equation for Argon Gas Cluster Sputtering Yields. Journal of Physical Chemistry C, 2013, 117, 12622-12632.	3.1	134
29	Modelling of surface nanoparticle inclusions for nanomechanical measurements by an AFM or nanoindenter: spatial issues. Nanotechnology, 2012, 23, 165704.	2.6	14
30	Identification and separation of protein, contaminant and substrate peaks using gentleâ€secondary ion mass spectrometry and the gâ€ogram. Rapid Communications in Mass Spectrometry, 2012, 26, 2815-2821.	1.5	10
31	Argon Cluster Ion Beams for Organic Depth Profiling: Results from a VAMAS Interlaboratory Study. Analytical Chemistry, 2012, 84, 7865-7873.	6.5	129
32	Sputtering Yields of Gold Nanoparticles by C₆₀ Ions. Journal of Physical Chemistry C, 2012, 116, 9311-9318.	3.1	34
33	Sputtering Yields for Gold Using Argon Gas Cluster Ion Beams. Journal of Physical Chemistry C, 2012, 116, 23735-23741.	3.1	21
34	Linearity of the instrumental intensity scale in TOFâ€SIMSâ€”a VAMAS interlaboratory study. Surface and Interface Analysis, 2012, 44, 1-14.	1.8	18
35	Topography effects and monatomic ion sputtering of undulating surfaces, particles and large nanoparticles: Sputtering yields, effective sputter rates and topography evolution. Surface and Interface Analysis, 2012, 44, 208-218.	1.8	23
36	Topography and field effects in secondary ion mass spectrometry Part II: insulating samples. Surface and Interface Analysis, 2012, 44, 238-245.	1.8	29

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37	An accurate and simple universal curve for the energyâ€dependent electron inelastic mean free path. Surface and Interface Analysis, 2012, 44, 497-503.	1.8	73
38	Summary of ISO/TC 201 Standard: ISO 18115-1:2010 - surface chemical analysis - vocabulary - general terms and terms used in spectroscopy. Surface and Interface Analysis, 2012, 44, 618-620.	1.8	6
39	Summary of ISO/TC 201 Standard: ISO 14701:2011 - Surface chemical analysis - X-ray photoelectron spectroscopy-measurement of silicon oxide thickness. Surface and Interface Analysis, 2012, 44, 876-878.	1.8	7
40	Summary of ISO/TC 201 Standard: ISO 18115-2:2010 - Surface chemical analysis - Vocabulary-Terms used in scanning probe microscopy. Surface and Interface Analysis, 2012, 44, 879-880.	1.8	4
41	Simple universal curve for the energyâ€dependent electron attenuation length for all materials. Surface and Interface Analysis, 2012, 44, 1353-1359.	1.8	106
42	Nanomechanical measurements of hair as an example of micro-fibre analysis using atomic force microscopy nanoindentation. Ultramicroscopy, 2012, 114, 38-45.	1.9	17
43	Mass Spectrometry and Informatics: Distribution of Molecules in the PubChem Database and General Requirements for Mass Accuracy in Surface Analysis. Analytical Chemistry, 2011, 83, 3239-3243.	6.5	20
44	Topography and Field Effects in Secondary Ion Mass Spectrometry â€“ Part I: Conducting Samples. Journal of the American Society for Mass Spectrometry, 2011, 22, 1718-28.	2.8	43
45	Cluster primary ion sputtering: correlations in secondary ion intensities in TOF SIMS. Surface and Interface Analysis, 2011, 43, 228-235.	1.8	12
46	Attenuation lengths in organic materials. Surface and Interface Analysis, 2011, 43, 744-751.	1.8	31
47	Analysis of thin films and molecular orientation using cluster SIMS. Surface and Interface Analysis, 2011, 43, 1224-1230.	1.8	4
48	VAMAS interlaboratory study on organic depth profiling. Surface and Interface Analysis, 2011, 43, 1240-1250.	1.8	28
49	Depth resolution and inhomogeneity of the sputtering dose with sample rotation and ion beam rastering. Surface and Interface Analysis, 2011, 43, 1430-1435.	1.8	6
50	Energy dependence of the electron attenuation length in silicon dioxide. Measurement Science and Technology, 2011, 22, 115602.	2.6	3
51	Surface and Interface Characterization. , 2011, , 281-335.		4
52	Sputtering yields of compounds using argon ions. Journal Physics D: Applied Physics, 2010, 43, 253001.	2.8	105
53	Relationships between cluster secondary ion mass intensities generated by different cluster primary ions. Journal of the American Society for Mass Spectrometry, 2010, 21, 370-377.	2.8	11
54	Approaches to analyzing insulators with Auger electron spectroscopy: Update and overview. Journal of Electron Spectroscopy and Related Phenomena, 2010, 176, 80-94.	1.7	33

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55	Correlations for predicting the surface wettability for organic light-emitting-diode patterns by x-ray photoelectron spectroscopy analysis. Journal of Applied Physics, 2010, 108, 114901.	2.5	0
56	Organic Depth Profiling of a Nanostructured Delta Layer Reference Material Using Large Argon Cluster Ions. Analytical Chemistry, 2010, 82, 98-105.	6.5	152
57	Cluster Primary Ion Sputtering: Secondary Ion Intensities in Static SIMS of Organic Materials. Journal of Physical Chemistry C, 2010, 114, 5351-5359.	3.1	23
58	Nanoindentation measurement of Youngâ€™s modulus for compliant layers on stiffer substrates including the effect of Poissonâ€™s ratios. Nanotechnology, 2009, 20, 145708.	2.6	34
59	Gâ€SIMS: relative effectiveness of different monatomic primary ion source combinations. Rapid Communications in Mass Spectrometry, 2009, 23, 599-602.	1.5	7
60	Ultraâ€thin SiO₂ on Si IX: absolute measurements of the amount of silicon oxide as a thickness of SiO₂ on Si. Surface and Interface Analysis, 2009, 41, 430-439.	1.8	39
61	Angular accuracy and the comparison of two methods for determining the surface normal in a Kratos Axis Ultra Xâ€ray photoelectron spectrometer. Surface and Interface Analysis, 2009, 41, 960-965.	1.8	4
62	Stoichiometric MgB2 layers produced by multi-energy implantation of boron into magnesium. Surface and Coatings Technology, 2009, 203, 2712-2716.	4.8	1
63	Analysis Of The Interface And Its Position In C60n+ Secondary Ion Mass Spectrometry Depth Profiling. Analytical Chemistry, 2009, 81, 75-79.	6.5	29
64	Developing Repeatable Measurements for Reliable Analysis of Molecules at Surfaces Using Desorption Electrospray Ionization. Analytical Chemistry, 2009, 81, 2286-2293.	6.5	55
65	Simplified drift characterization in scanning probe microscopes using a simple two-point method. Measurement Science and Technology, 2009, 20, 095103.	2.6	23
66	Improved methods and uncertainty analysis in the calibration of the spring constant of an atomic force microscope cantilever using static experimental methods. Measurement Science and Technology, 2009, 20, 125501.	2.6	31
67	Artifacts in the sputtering of inorganics by C60n+. Applied Surface Science, 2008, 255, 934-937.	6.1	12
68	Imaging Gâ€SIMS: a novel bismuthâ€manganese source emitter. Rapid Communications in Mass Spectrometry, 2008, 22, 2602-2608.	1.5	28
69	Cluster ion beam profiling of organics by secondary ion mass spectrometry â€“ does sodium affect the molecular ion intensity at interfaces?. Rapid Communications in Mass Spectrometry, 2008, 22, 4178-4182.	1.5	4
70	Summary of ISO/TC 201 standard: XXXIII, ISO 18115:2001/Amd. 2:2007-Surface Chemical Analysis-Vocabulary-Amendment 2. Surface and Interface Analysis, 2008, 40, 1500-1502.	1.8	7
71	G-SIMS and SMILES: Simulated fragmentation pathways for identification of complex molecules, amino acids and peptides. Applied Surface Science, 2008, 255, 852-855.	6.1	8
72	Topography and field effects in the quantitative analysis of conductive surfaces using ToF-SIMS. Applied Surface Science, 2008, 255, 1560-1563.	6.1	41

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73	Identification of complex molecules at surfaces: G-SIMS and SMILES fragmentation pathways. International Journal of Mass Spectrometry, 2008, 272, 38-47.	1.5	23
74	On the applicability of XPS for quantitative total organic and elemental carbon analysis of airborne particulate matter. Atmospheric Environment, 2008, 42, 3888-3891.	4.1	23
75	Quantitative Molecular Depth Profiling of Organic Delta-Layers by C60 Ion Sputtering and SIMS. Journal of Physical Chemistry B, 2008, 112, 2596-2605.	2.6	119
76	Cluster primary ions: Spikes, sputtering yields, secondary ion yields, and interrelationships for secondary molecular ions for static secondary ion mass spectrometry. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2008, 26, 660-667.	2.1	2
77	Modelling of Nanoindentation of Compliant Layers on Stiffer Substrates using Finite Element Analysis. Materials Research Society Symposia Proceedings, 2007, 1025, 1.	0.1	0
78	Comparison of the accuracies of two methods for the determination of the surface normal for x-ray photoelectron spectroscopy. Metrologia, 2007, 44, 242-245.	1.2	2
79	Summary of ISO/TC 201 Standard: XXIII, ISO 24236:2005â€"surface chemical analysisâ€"Auger electron spectroscopyâ€"repeatability and constancy of intensity scale. Surface and Interface Analysis, 2007, 39, 86-88.	1.8	5
80	Summary of ISO/TC 201 Standard: XXVIII, ISO 18115:2001/Amd. 1:2006â€"surface chemical analysisâ€"vocabularyâ€"amendment 1. Surface and Interface Analysis, 2007, 39, 367-369.	1.8	7
81	Summary of ISO/TC 201 Standard: XXIV, ISO 24237:2005â€"surface chemical analysisâ€"X-ray photoelectron spectroscopyâ€"repeatability and constancy of intensity scale. Surface and Interface Analysis, 2007, 39, 370-372.	1.8	9
82	Accurate measurement of sputtered depth for ion sputtering rates and yields: the mesh replica method. Surface and Interface Analysis, 2007, 39, 69-78.	1.8	1
83	Ultra-thin SiO2 on Si VIII. Accuracy of method, linearity and attenuation lengths for XPS. Surface and Interface Analysis, 2007, 39, 512-518.	1.8	31
84	Analysis of cluster ion sputtering yields: correlation with the thermal spike model and implications for static secondary ion mass spectrometry. Surface and Interface Analysis, 2007, 39, 634-643.	1.8	37
85	Cluster ion sputtering: molecular ion yield relationships for different cluster primary ions in static SIMS of organic materials. Surface and Interface Analysis, 2007, 39, 890-897.	1.8	29
86	Comment on â€œIdentification of background in CMAâ€•[J. Surf. Anal. 14, 95 (2007)]. Journal of Surface Analysis (Online), 2007, 14, 169-169.	0.1	0
87	Surface and Interface Characterization. , 2006, , 229-280.		3
88	The Spirit of ECASIA. Surface and Interface Analysis, 2006, 38, 163-163.	1.8	1
89	Repeatable intensity calibration of an X-ray photoelectron spectrometer. Journal of Electron Spectroscopy and Related Phenomena, 2006, 151, 178-181.	1.7	15
90	Mass accuracyâ€"TOF-SIMS. Applied Surface Science, 2006, 252, 6591-6593.	6.1	4

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91	G-SIMS-FPM: Molecular structure at surfacesâ€"a combined positive and negative secondary ion study. Applied Surface Science, 2006, 252, 6601-6604.	6.1	17
92	TOF-SIMS: Accurate mass scale calibration. Journal of the American Society for Mass Spectrometry, 2006, 17, 514-523.	2.8	71
93	Modelling of nanomechanical nanoindentation measurements using an AFM or nanoindenter for compliant layers on stiffer substrates. Nanotechnology, 2006, 17, 5283-5292.	2.6	76
94	Erratum to â€œAn accurate semi-empirical equation for sputtering yields, II: for neon, argon and xenon ionsâ€•[Nucl. Instr. and Meth. B 229 (2005) 348â€“358]. Nuclear Instruments & Methods in Physics Research B, 2005, 239, 286-287.	1.4	10
95	An accurate semi-empirical equation for sputtering yields, II: for neon, argon and xenon ions. Nuclear Instruments & Methods in Physics Research B, 2005, 229, 348-358.	1.4	62
96	Quantification issues in the identification of nanoscale regions of homopolymers using modulus measurement via AFM nanoindentation. Applied Surface Science, 2005, 252, 1915-1933.	6.1	147
97	Ultrathin SiO2 on Si. VI. Evaluation of uncertainties in thickness measurement using XPS. Surface and Interface Analysis, 2005, 37, 300-309.	1.8	37
98	An accurate semi-empirical equation for sputtering yields I: for argon ions. Surface and Interface Analysis, 2005, 37, 444-458.	1.8	112
99	Ultrathin SiO2 on Si. VII. Angular accuracy in XPS and an accurate attenuation length. Surface and Interface Analysis, 2005, 37, 731-736.	1.8	51
100	The determination of atomic force microscope cantilever spring constants via dimensional methods for nanomechanical analysis. Nanotechnology, 2005, 16, 1666-1680.	2.6	166
101	Critical review of the current status of thickness measurements for ultrathin SiO2 on Si Part V: Results of a CCQM pilot study. Surface and Interface Analysis, 2004, 36, 1269-1303.	1.8	138
102	Organic molecule characterizationâ€"G-SIMS. Applied Surface Science, 2004, 231-232, 224-229.	6.1	28
103	G-SIMS of crystallisable organics. Applied Surface Science, 2003, 203-204, 551-555.	6.1	31
104	Summary of ISO/TC 201 Standard XI. ISO 17974:2002?Surface chemical analysis?High-resolution Auger electron spectrometers?Calibration of energy scales for elemental and chemical-state analysis. Surface and Interface Analysis, 2003, 35, 327-328.	1.8	12
105	Summary of ISO/TC 201 Standard XII. ISO 17973:2002?Surface chemical analysis?Medium-resolution Auger electron spectrometers?Calibration of energy scales for elemental analysis. Surface and Interface Analysis, 2003, 35, 329-330.	1.8	11
106	Ultrathin SiO2 on Si IV. Intensity measurement in XPS and deduced thickness linearity. Surface and Interface Analysis, 2003, 35, 515-524.	1.8	109
107	Degradation of poly(vinyl chloride) and nitrocellulose in XPS. Surface and Interface Analysis, 2003, 35, 906-913.	1.8	14
108	Investigating the difficulty of eliminating flood gun damage in TOF-SIMS. Applied Surface Science, 2003, 203-204, 600-604.	6.1	18

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109	Electron flood gun damage in the analysis of polymers and organics in time-of-flight SIMS. Applied Surface Science, 2002, 187, 89-100.	6.1	66
110	The Spirit of ECASIA. Surface and Interface Analysis, 2002, 34, 1-1.	1.8	2
111	Ultrathin SiO2 on Si II. Issues in quantification of the oxide thickness. Surface and Interface Analysis, 2002, 33, 640-652.	1.8	195
112	Resolution parameters for model functions used in surface analysis. Surface and Interface Analysis, 2002, 33, 950-953.	1.8	21
113	Ultrathin SiO2 on Si: III mapping the layer thickness efficiently by XPS. Surface and Interface Analysis, 2002, 33, 960-963.	1.8	39
114	Quantitative AES and XPS:. Journal of Surface Analysis (Online), 2002, 9, 275-280.	0.1	2
115	Background subtraction III. Surface Science, 2001, 471, 185-202.	1.9	18
116	Quantitative XPS. Journal of Electron Spectroscopy and Related Phenomena, 2001, 120, 93-111.	1.7	163
117	Summary of ISO/TC 201 Standard: VII ISO 15472 : 2001?surface chemical analysis?x-ray photoelectron spectrometers?calibration of energy scales. Surface and Interface Analysis, 2001, 31, 721-723.	1.8	200
118	Quantitative AES IX and quantitative XPS II: Auger and x-ray photoelectron intensities and sensitivity factors from spectral digital databases reanalysed using a REELS database. Surface and Interface Analysis, 2001, 31, 778-795.	1.8	63
119	Simplified equations for correction parameters for elastic scattering effects in AES and XPS forQ, ? and attenuation lengths. Surface and Interface Analysis, 2001, 31, 835-846.	1.8	87
120	Summary of ISO/TC 201 Standard: VIII, ISO 18115:2001?Surface chemical analysis?Vocabulary. Surface and Interface Analysis, 2001, 31, 1048-1049.	1.8	19
121	Ion detection efficiency in SIMS:. International Journal of Mass Spectrometry, 2000, 202, 217-229.	1.5	117
122	Static SIMS: towards unfragmented mass spectra â€" the G-SIMS procedure. Applied Surface Science, 2000, 161, 465-480.	6.1	82
123	AES of bulk insulators â€" control and characterisation of the surface charge. Journal of Electron Spectroscopy and Related Phenomena, 2000, 109, 291-308.	1.7	48
124	Background subtraction. Surface Science, 2000, 461, 1-15.	1.9	60
125	Signal linearity in XPS counting systems. Journal of Electron Spectroscopy and Related Phenomena, 1999, 104, 73-89.	1.7	24
126	Quantitative AES and XPS: convergence between theory and experimental databases. Journal of Electron Spectroscopy and Related Phenomena, 1999, 100, 55-73.	1.7	37

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127	Static SIMS: metastable decay and peak intensities. Applied Surface Science, 1999, 144-145, 26-30.	6.1	11
128	Static SIMS: ion detection efficiencies in a channel electron multiplier. Applied Surface Science, 1999, 144-145, 113-117.	6.1	8
129	Reference data for Auger electron spectroscopy and X-ray photoelectron spectroscopy combined. Applied Surface Science, 1999, 144-145, 161-167.	6.1	11
130	Method for determining the signal linearity in single and multidetector counting systems in X-ray photoelectron spectroscopy. Applied Surface Science, 1999, 144-145, 132-136.	6.1	2
131	Background subtraction. Surface Science, 1999, 420, 285-294.	1.9	72
132	AES: energy calibration of electron spectrometers. IV. A re-evaluation of the reference energies. Journal of Electron Spectroscopy and Related Phenomena, 1998, 97, 235-241.	1.7	27
133	Validation and accuracy of software for peak synthesis in XPS. Journal of Electron Spectroscopy and Related Phenomena, 1998, 95, 71-93.	1.7	45
134	AES: energy calibration of electron spectrometers. Ill â€" General calibration rules. Journal of Electron Spectroscopy and Related Phenomena, 1997, 83, 197-208.	1.7	13
135	The alignment of spectrometers and quantitative measurements in X-ray photoelectron spectroscopy. Journal of Electron Spectroscopy and Related Phenomena, 1997, 87, 159-167.	1.7	9
136	Savitzky and Golay differentiation in AES. Applied Surface Science, 1996, 93, 273-280.	6.1	8
137	Stability of reference masses. IV: Growth of carbonaceous contamination on platinum-iridium alloy surfaces, and cleaning by UV/ozone treatment. Metrologia, 1996, 33, 507-532.	1.2	39
138	Static SIMS: Surface charge stabilization of insulators for highly repeatable spectra when using a quadrupole mass spectrometer. Surface and Interface Analysis, 1995, 23, 191-203.	1.8	16
139	Fluence, flux, current and current density measurement in faraday cups for surface analysis. Surface and Interface Analysis, 1995, 23, 248-258.	1.8	14
140	Effective dead time in pulse counting systems. Surface and Interface Analysis, 1995, 23, 729-732.	1.8	25
141	A system for the intensity calibration of electron spectrometers. Journal of Electron Spectroscopy and Related Phenomena, 1995, 71, 191-204.	1.7	86
142	Stability of Reference Masses III: Mechanism and Long-term Effects of Mercury Contamination on Platinum-Iridium Mass Standards. Metrologia, 1995, 31, 375-388.	1.2	15
143	Comment on â€˜neglected and hidden errors in the quantification of Auger electron spectroscopyâ€™ by J. du plessis (Surf. Interface Anal. 20, 228 (1993)). Surface and Interface Analysis, 1994, 21, 587-589.	1.8	5
144	Optimisation and specification of Auger electron spectrometers for signal-to-noise ratio performance. Journal of Electron Spectroscopy and Related Phenomena, 1994, 67, 151-157.	1.7	7

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145	Stability of Reference Masses II: The Effect of Environment and Cleaning Methods on the Surfaces of Stainless Steel and Allied Materials. Metrologia, 1994, 31, 93-108.	1.2	36
146	Stability of Reference Masses I: Evidence for Possible Variations in the Mass of Reference Kilograms Arising from Mercury Contamination. Metrologia, 1994, 31, 21-26.	1.2	29
147	Signal-to-noise ratio assessment and measurement in spectroscopies with particular reference to Auger and X-ray photoelectron spectroscopies. Journal of Electron Spectroscopy and Related Phenomena, 1993, 61, 291-308.	1.7	13
148	Development of a reference material and reference method to provide a calibration of the instrument intensity scale for differential AES. Journal of Electron Spectroscopy and Related Phenomena, 1993, 61, 149-171.	1.7	5
149	Interlaboratory tests of a composite reference sample to calibrate Auger electron spectrometers in the differential mode. Journal of Electron Spectroscopy and Related Phenomena, 1993, 61, 173-182.	1.7	4
150	AES and XPS measurements: reducing the uncertainty and improving the accuracy. Applied Surface Science, 1993, 70-71, 1-8.	6.1	5
151	XPS reference procedure for the accurate intensity calibration of electron spectrometers? results of a BCR intercomparison co-sponsored by the VAMAS SCA TWA. Surface and Interface Analysis, 1993, 20, 243-266.	1.8	132
152	Scattering in electron spectrometers, diagnosis and avoidance. I. Concentric hemispherical analysers. Surface and Interface Analysis, 1993, 20, 865-875.	1.8	25
153	Scattering in electron spectrometers, diagnosis and avoidance. II. Cylindrical mirror analysers. Surface and Interface Analysis, 1993, 20, 876-890.	1.8	16
154	Reassessment of energy transfers in the quasielastic scattering of 250â€“3000 eV electrons at surfaces. Physical Review B, 1993, 47, 9836-9839.	3.2	31
155	Submonolayer adsorbate reference material based on a low alloy steel fracture sample for Auger electron spectroscopy Part 1 Characterisation. Materials Science and Technology, 1992, 8, 1023-1035.	1.6	7
156	Submonolayer adsorbate reference material based on a low alloy steel fracture sample for Auger electron spectroscopy Part 2 Interlaboratory tests. Materials Science and Technology, 1992, 8, 1036-1042.	1.6	3
157	Linearity in electron counting and detection systems. Surface and Interface Analysis, 1992, 18, 240-246.	1.8	30
158	Random uncertainties in AES and XPS: I: Uncertainties in peak energies, intensities and areas derived from peak synthesis. Surface and Interface Analysis, 1992, 18, 345-360.	1.8	84
159	Random uncertainties in AES and XPS: II: Quantification using either relative or absolute measurements. Surface and Interface Analysis, 1992, 18, 361-367.	1.8	18
160	Comment on â€˜spectral noise removal by digital filtering and its application to surface analysisâ€™ by K. Piyakis and E. Sacher. Applied Surface Science, 1992, 62, 195-198.	6.1	6
161	Versailles project on advanced materials and standards study of intensity stability of cylindrical mirror analyser-based Auger electron spectrometers. Journal of Electron Spectroscopy and Related Phenomena, 1992, 58, 345-357.	1.7	11
162	AES: Accurate intensity calibration of electron spectrometersâ€”results of a BCR interlaboratory comparison co-sponsored by the VAMAS SCA TWP. Surface and Interface Analysis, 1991, 17, 855-874.	1.8	61

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163	Energy and spatial dependence of the electron detection efficiencies of single channel electron multipliers used in electron spectroscopy. Review of Scientific Instruments, 1991, 62, 62-68.	1.3	18
164	Method for the alignment of samples and the attainment of ultra-high-resolution depth profiles in Auger electron spectroscopy. Surface and Interface Analysis, 1990, 15, 254-258.	1.8	10
165	AES: Energy calibration of electron spectrometers. I?an absolute, traceable energy calibration and the provision of atomic reference line energies. Surface and Interface Analysis, 1990, 15, 293-308.	1.8	165
166	AES: Energy calibration of electron spectrometers. II?results of a BCRinterlaboratory comparison co-sponsored by the vamas SCS TWP. Surface and Interface Analysis, 1990, 15, 309-322.	1.8	11
167	Quatitative AES: Reducing errors in measured analogue spectral intensities through control of the electron detector. Surface and Interface Analysis, 1990, 15, 701-704.	1.8	5
168	Quantitative AES and XPS: Determination of the electron spectrometer transmission function and the detector sensitivity energy dependencies for the production of true electron emission spectra in AES and XPS. Surface and Interface Analysis, 1990, 15, 751-766.	1.8	97
169	Channel electron multipliers: quantitative intensity measurementâ€"efficiency, gain, linearity and bias effects. Journal of Electron Spectroscopy and Related Phenomena, 1990, 50, 137-157.	1.7	68
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